



CLEAN VERSION OF AMENDED SPECIFICATION PARAGRAPHS

METHOD TO REDUCE TRANSISTOR CHANNEL LENGTH USING SDOX

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On page 2, paragraph 5:

As shown in Figure 2c, in the oxidizing process, oxygen is diffused into the gate 220 from the side to form the first side oxide region 236 as shown by arrows 244. Oxygen is also diffused through the gate oxide 210 and into the bottom of the gate 220 to form the first bottom oxide region 238 as shown by arrow 246.

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